

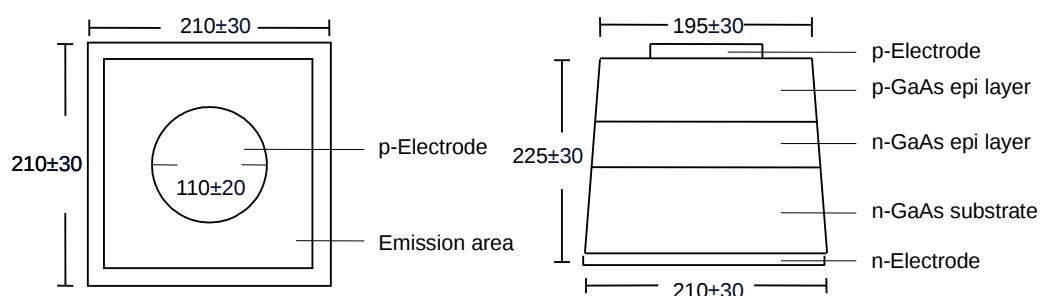
■ Features :

- GaAs/GaAs Wafer
- Good Spectral Matched to Si Detector

■ Typical Applications :

- Peripheral Device
- Photo Coupler
- Photo Interrupter

■ Outline Dimensions : (Unit: μm)



■ Physical Structure :

Chip dimension	Chip size	210±30 μm x 210±30 μm
	Thickness	225±30 μm
	Emission area	195±30 μm
	Bonding pad	110±20 μm
Electrode	Top: P (anode)	Aluminum
	Backside: N (cathode)	Gold alloy
Surface condition	Smooth	

■ Electro-Optical Characteristics : ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	-	1.25	1.50	V
		$I_F = 100 \text{ mA}$	-	1.48	1.90	
Reverse Voltage	V_R	$I_R = 10 \text{ uA}$	5	-	-	V
Wavelength	λ_P	$I_F = 20 \text{ mA}$	-	940	-	nm
Spectral width at half height	$\Delta \lambda$	$I_F = 20 \text{ mA}$	-	50	-	nm
Radiant Power	P_o	$I_F = 20 \text{ mA}$	0.20	-	-	mW

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

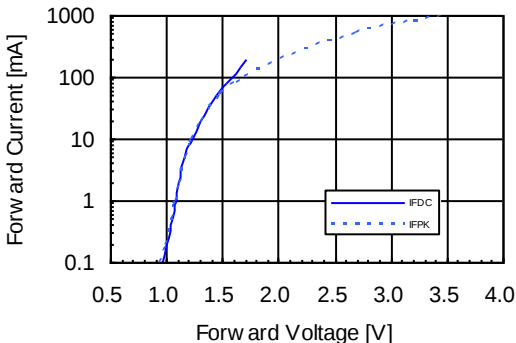


Fig 2. Relative Radiant Power vs. Wavelength

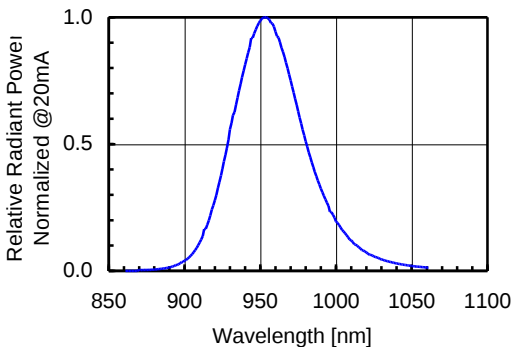


Fig 3. Relative Radiant Power
vs. Forward DC Current

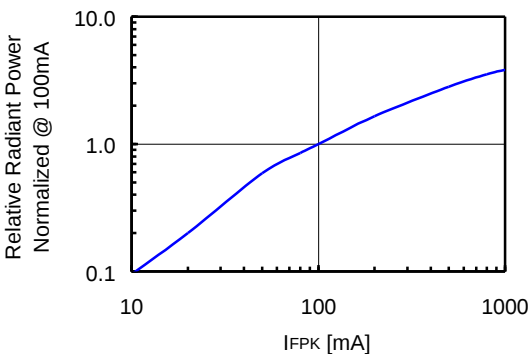


Fig 4. Relative Radiant Power
vs. Forward Peak Current

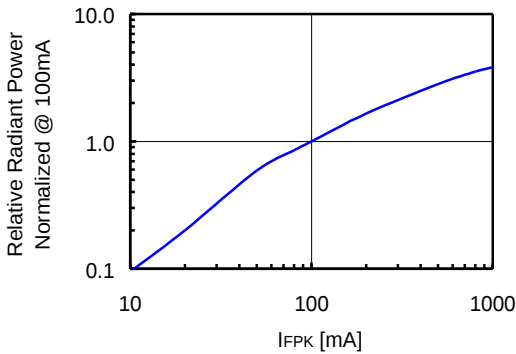


Fig 5. Forward DC Voltage vs. Temperature

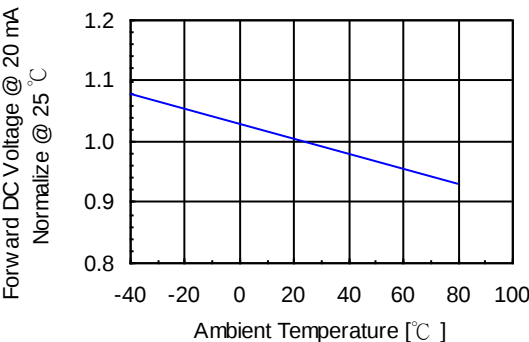


Fig 6. Relative Radiant Power vs. Temperature

